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Abstract (en)
[origin: WO03056630A2] The invention relates to a transistor comprising an emitter (1), a collector (2) and a base layer (3). According to the invention, the emitter (1) extends into the base layer (3); the base layer (3) comprises an intrinsic region (4) located between the emitter (1) and the collector (2), and an extrinsic region (6) extending between the intrinsic region (4) and a base contact (5); and said base layer (3) also contains a first layer (7) which is doped with a trivalent dopant, extends into the extrinsic region (6), and is counter-doped in the region of the emitter (1) by a pentavalent counter-dopant (8). The electrical resistance of the base layer (3) can be advantageously reduced due to said first doped layer (7).

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